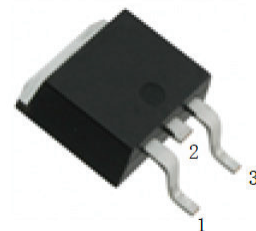
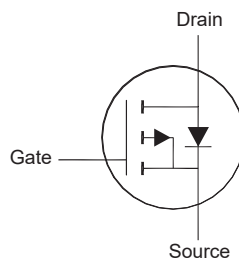


P-Channel Enhancement Mode MOSFET

Features

- Surface-mounted package
- Halogen and Antimony Free(HAF), RoHS compliant



1.Gate 2.Drain 3.Source
TO-252 Plastic Package

Key Parameters

Parameter	Value	Unit
$-BV_{DS}$	40	V
$R_{DS(ON)} \text{ Max}$	7.6 @ $-V_{GS} = 10 \text{ V}$	m Ω
$-V_{GS(th)} \text{ typ}$	3.1	V
$Q_g \text{ typ}$	105 @ $-V_{GS} = 10 \text{ V}$	nC

Absolute Maximum Ratings (at $T_a = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$-V_{DS}$	40	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current	$-I_D$	84 58.8	A
Peak Drain Current ¹⁾	$-I_{DM}$	350	A
Avalanche Current	$-I_{AS}$	66.5	A
Avalanche Energy ²⁾	E_{AS}	221	mJ
Power Dissipation	P_{tot}	83.3	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to + 175	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Max.	Unit
Thermal Resistance from Junction to Case	$R_{\theta JC}$	1.8	$^\circ\text{C/W}$
Thermal Resistance from Junction to Ambient ³⁾	$R_{\theta JA}$	38	$^\circ\text{C/W}$

¹⁾ Pulse Test: Pulse Width $\leq 100 \mu\text{s}$, Duty Cycle $\leq 2\%$, Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)} = 175^\circ\text{C}$.

²⁾ Limited by $T_{J(MAX)}$, starting $T_J = 25^\circ\text{C}$, $L = 0.1 \text{ mH}$, $R_g = 25 \Omega$, $-I_{AS} = 66.5 \text{ A}$, $-V_{GS} = 10 \text{ V}$.

³⁾ Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate in still air.

Characteristics at T_a = 25°C unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit
STATIC PARAMETERS					
Drain-Source Breakdown Voltage at $-I_D = 250 \mu A$	$-V_{(BR)DSS}$	40	-	-	V
Drain-Source On-State Current at $-V_{DS} = 32 V$	$-I_{DSS}$	-	-	1	μA
Gate-Source Leakage Current at $V_{GS} = \pm 16 V$	I_{GSS}	-	-	± 100	nA
Gate-Source Threshold Voltage at $V_{DS} = V_{GS}$, $-I_D = 250 \mu A$	$-V_{GS(th)}$	2	-	4	V
Drain-Source On-State Resistance at $-V_{GS} = 10 V$, $-I_D = 30 A$	$R_{DS(ON)}$	-	6.4	7.6	m Ω
DYNAMIC PARAMETERS					
Forward Transconductance at $-V_{DS} = 5 V$, $-I_D = 10 A$	g_{fs}	-	29	-	S
Gate resistance at $V_{GS} = 0 V$, $V_{DS} = 0 V$, $f = 1 MHz$	R_g	-	2	-	Ω
Input Capacitance at $V_{GS} = 0 V$, $-V_{DS} = 20 V$, $f = 1 MHz$	C_{iss}	-	7475	-	pF
Output Capacitance at $V_{GS} = 0 V$, $-V_{DS} = 20 V$, $f = 1 MHz$	C_{oss}	-	555	-	pF
Reverse Transfer Capacitance at $V_{GS} = 0 V$, $-V_{DS} = 20 V$, $f = 1 MHz$	C_{rss}	-	329	-	pF
Total Gate Charge at $-V_{GS} = 10 V$, $-V_{DS} = 20 V$, $-I_D = 20 A$	Q_g	-	105	-	nC
Gate-Source Charge at $-V_{GS} = 10 V$, $-V_{DS} = 20 V$, $-I_D = 20 A$	Q_{gs}	-	38	-	nC
Gate-Drain Charge at $-V_{GS} = 10 V$, $-V_{DS} = 20 V$, $-I_D = 20 A$	Q_{gd}	-	18	-	nC
Turn-On Delay Time at $-V_{GS} = 10 V$, $-V_{DD} = 20 V$, $-I_D = 20 A$, $R_g = 3.3 \Omega$	$t_{d(on)}$	-	44	-	ns
Turn-On Rise Time at $-V_{GS} = 10 V$, $-V_{DD} = 20 V$, $-I_D = 20 A$, $R_g = 3.3 \Omega$	t_r	-	52	-	ns
Turn-Off Delay Time at $-V_{GS} = 10 V$, $-V_{DD} = 20 V$, $-I_D = 20 A$, $R_g = 3.3 \Omega$	$t_{d(off)}$	-	30	-	ns
Turn-Off Fall Time at $-V_{GS} = 10 V$, $-V_{DD} = 20 V$, $-I_D = 20 A$, $R_g = 3.3 \Omega$	t_f	-	10	-	ns
Body-Diode PARAMETERS					
Drain-Source Diode Forward Voltage at $-I_S = 1 A$, $V_{GS} = 0 V$	$-V_{SD}$	-	-	1.2	V
Body-Diode Continuous Current	$-I_S$	-	-	84	A
Body-Diode Continuous Current, Pulsed	$-I_{SM}$	-	-	350	A
Body Diode Reverse Recovery Time at $-I_S = 20 A$, $di/dt = 100 A / \mu s$	t_{rr}	-	26	-	ns
Body Diode Reverse Recovery Charge at $-I_S = 20 A$, $di/dt = 100 A / \mu s$	Q_{rr}	-	27	-	nC

Electrical Characteristics Curves

Fig. 1 Typical Output Characteristics

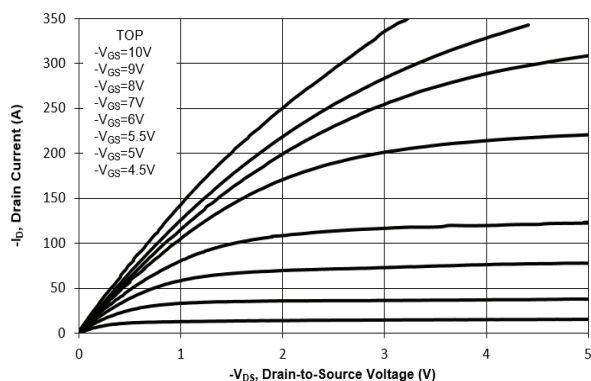


Fig. 2 Typical Transfer Characteristics

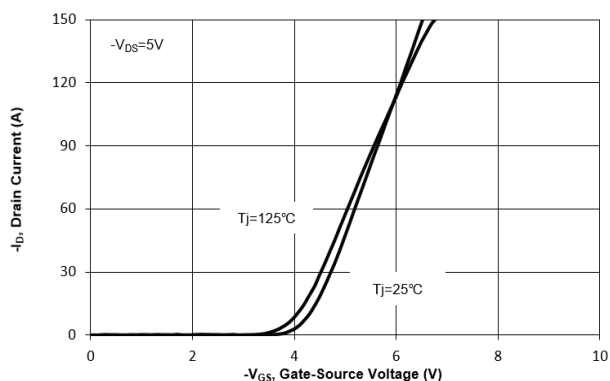


Fig. 3 on-Resistance vs Drain Current

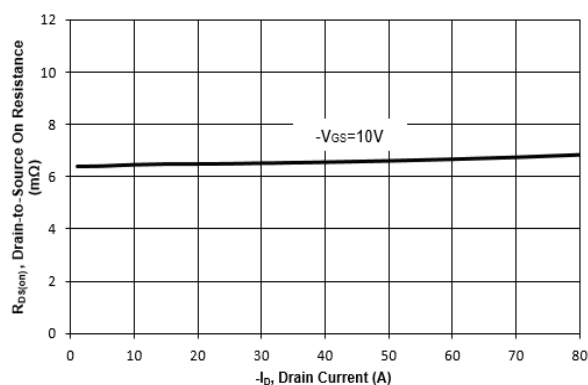


Fig. 4 on-Resistance vs. Gate to Source Voltage

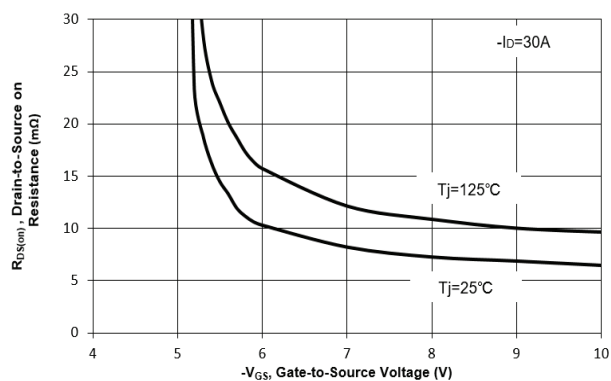


Fig. 5 on-Resistance vs. T_J

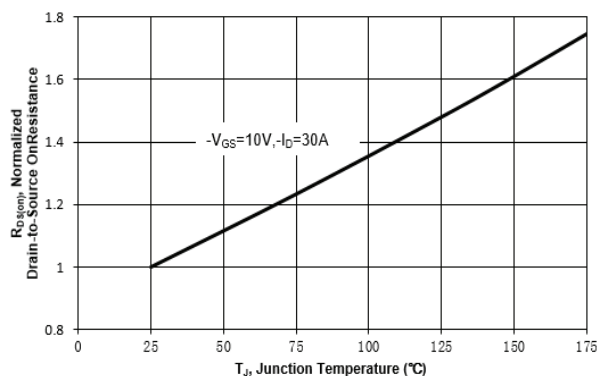
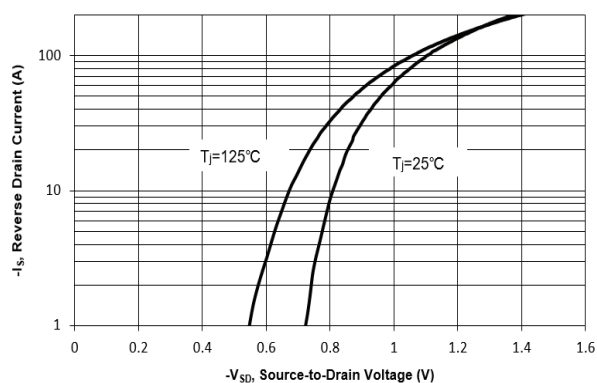


Fig. 6 Typical Body-Diode Forward Characteristics



Electrical Characteristics Curves

Fig. 7 Typical Junction Capacitance

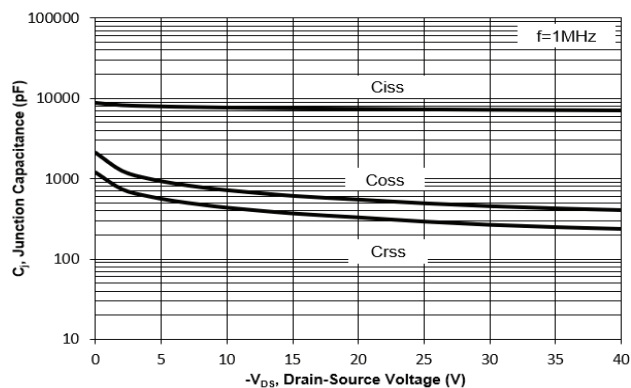


Fig. 8 Drain-Source Leakage Current vs. Tj

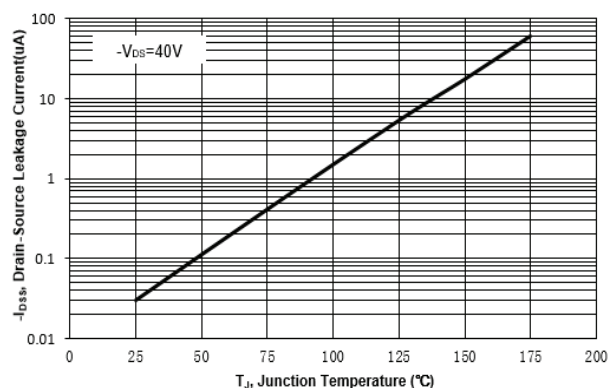


Fig. 9 V(BR)DSS vs. Junction Temperature

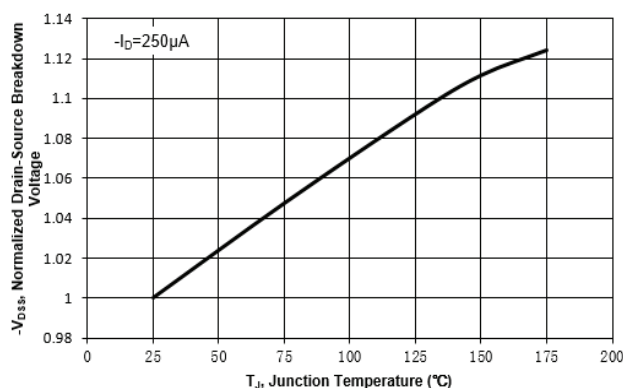


Fig. 10 Gate Threshold Variation vs. Tj

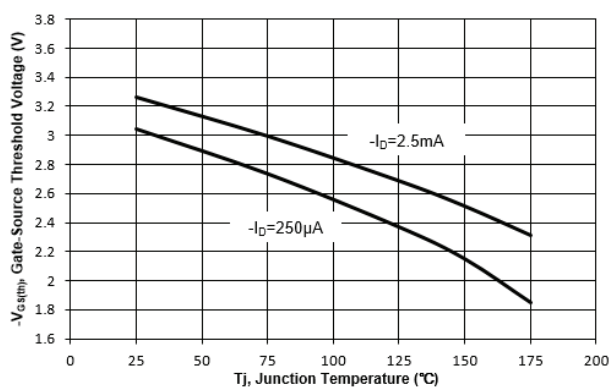


Fig. 11 Gate Charge

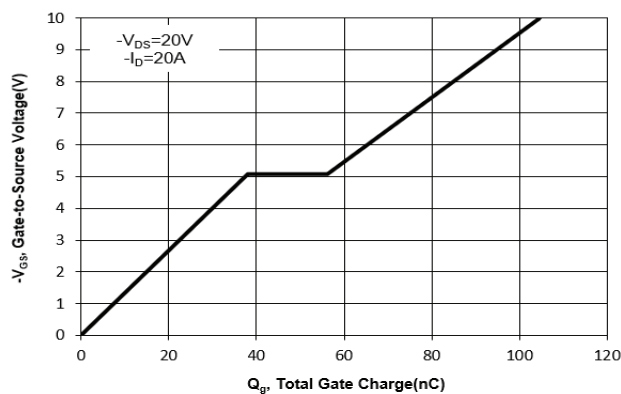
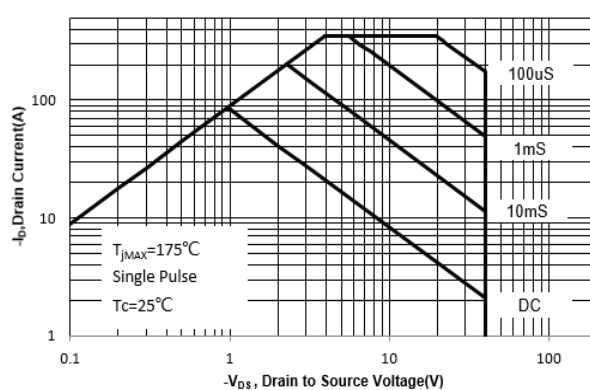


Fig. 12 Safe Operation Area



Electrical Characteristics Curves

Fig.13 Normalized Maximum Transient Thermal Impedance($z_{\theta JC}$)

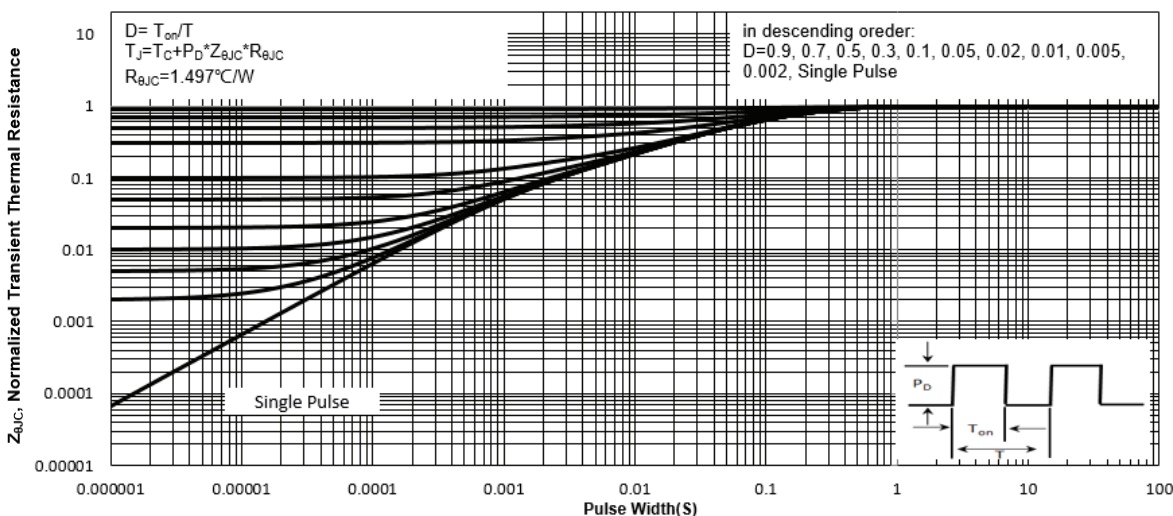
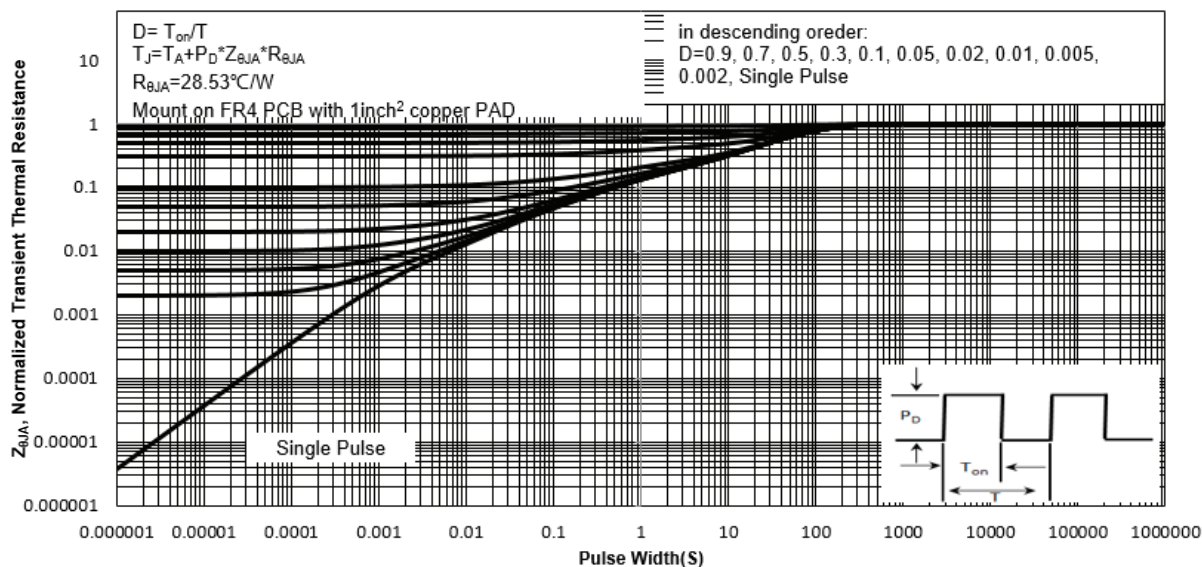


Fig.14 Normalized Maximum Transient Thermal Impedance($z_{\theta JA}$)



Test Circuits

Fig.1-1 Switching times test circuit

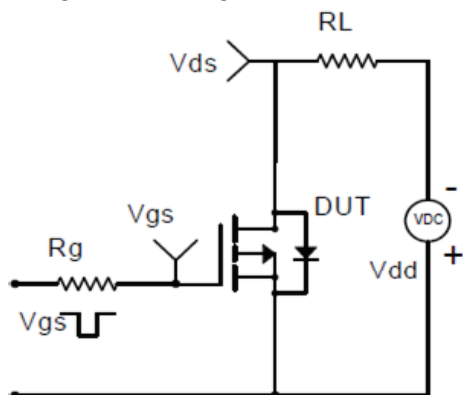


Fig.1-2 Switching Waveform

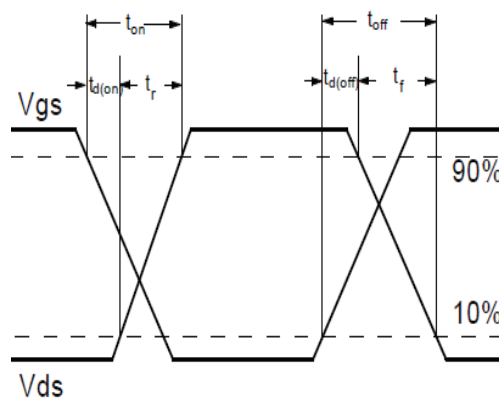


Fig.2-1 Gate charge test circuit

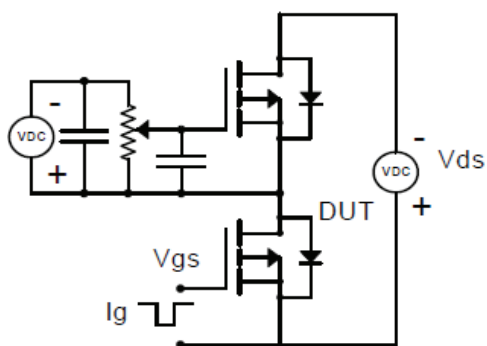


Fig.2-2 Gate charge waveform

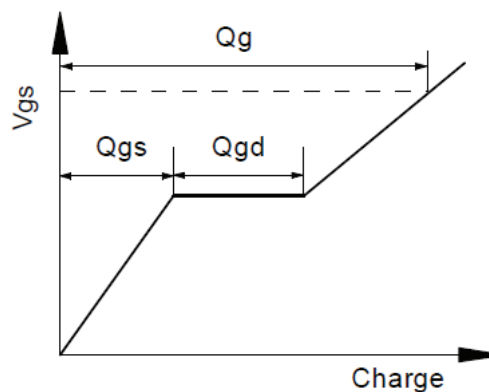


Fig.3-1 Avalanche test circuit

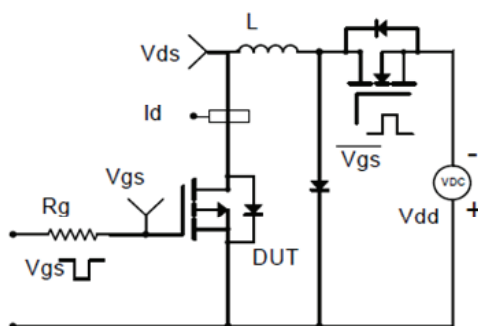
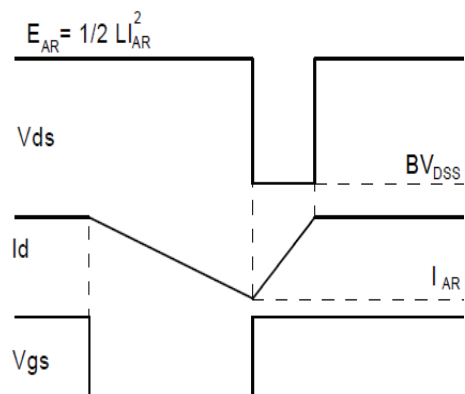
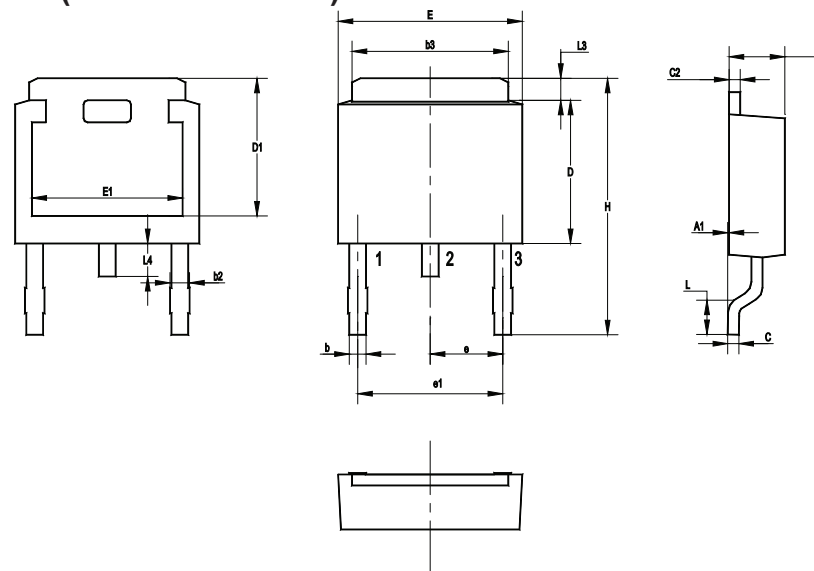


Fig.3-2 Avalanche waveform



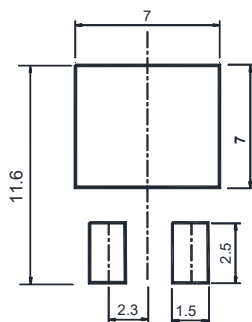
Package Outline (Dimensions in mm)

TO-252



UNIT	A	A1	b	b2	b3	C	C2	D	D1	E	E1	e	e1	H	L	L3	L4
mm	2.5	0.15	1.0	1.15	5.5	0.65	0.65	6.2	5.4	6.7	5.0	2.30	4.60	10.7	1.78	1.20	1.10
	2.1	0	0.5	0.65	4.9	0.4	0.4	5.6	5.0	6.1	4.6	TYP.	TYP.	9	1.40	0.85	0.51

Recommended Soldering Footprint



Packing information

Package	Tape Width (mm)	Pitch		Reel Size		Per Reel Packing Quantity
		mm	inch	mm	inch	
TO-252	16	8 ± 0.1	0.315 ± 0.004	330	13	2,500

Marking information

" TR04P047SS " = Part No.

" ***** " = Date Code Marking

Font type: Arial



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